25Gb/s Silicon-Photonics WDM Platform for Low-Power Optical I/O

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The adoption of silicon photonics as a viable technology for chip-level optical interconnects requires the co-integration in a single platform of high-performance silicon optical devices such as high-speed and low-voltage silicon modulators, highly responsive Ge photodetectors, as well as passive optical devices such as efficient fiber couplers and low-loss wavelength-division multiplexing filters. In this paper, we review the performance of imec's recently announced 200mm fully integrated 25Gb/s Silicon Photonics Platform [1]. We will discuss high-speed Si ring [2] and Mach-Zehnder modulators, high-speed Ge p-i-n photodetectors and passive devices such as ring-based DWDM filters [3] and arrayed-waveguide grating CWDM filters [4] demonstrated in this platform (see Fig. 1). In addition, we will discuss the recent demonstration of a highly efficient 10Gb/s 1.1V CMOS Photonics transmitter, comprising a Si ring modulator and a co-designed flip-chip integrated 40nm CMOS driver chip (see Fig. 2).

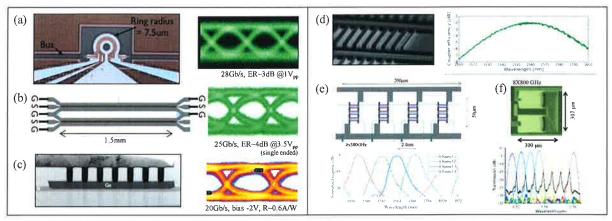


Fig. 1. (a) 28Gb/s Si ring modulator, (b) 25Gb/s traveling-wave Si MZ modulator, (c) 50GHz Ge p-i-n photodetector, (d) 2dB grating fiber coupler, (e) Si ring 4-ch DWDM filter [3], (f) Si AWG 8-ch CWDM filter [4].

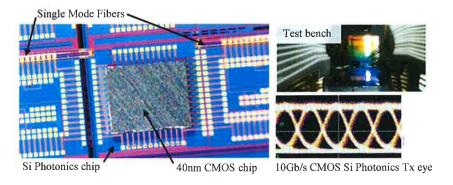


Fig. 2. 1.1V CMOS Si Photonics 10Gb/s Ring Transmitter demonstration [5].

References

- [1] http://www.europractice-ic.com/
- [2] M. Pantouvaki et al., in Proceedings "ECOC", IEEE (2013), paper We.3.B.2
- [3] P. De Heyn, et al., J. Lightwave Technol. 31, 2785-2792 (2013)
- [4] S. Pathak et al., in Proceedings "Group IV Photonics", IEEE (2013), paper WC7
- [5] M. Rakowski et al., in Proceedings "OFC/NFOEC", OSA (2013), paper OM2H.5

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15:50-16:10 Break

(Session B contd.)

16:10 **B-5**

Demonstration of 30-Tbps/cm² Bandwidth Density by Silicon Optical Interposers Fully Integrated with Optical Components

Y. Urino (PETRA/PECST)

16:25 B-6

Hybrid Integrated Light Source on a Si Platform Using a Quantum Dot Laser under Wide Temperature Range

M. Ishizaka (PETRA/PECST)

16:40 **B**-

Low-Voltage-Driven 50-Gb/s Ring-Resonator-Based Silicon Modulator

S. Akiyama (PETRA/PECST)

16:55 B-8

High Performance PIN Ge Photodetector and Si Optical Modulator

with MOS Junction

J. Fujikata (PETRA/PECST)

17:10 **B**-

Wide Wavelength and Temperature Tolerance

in 10 Gbps Photonic Crystal Modulators

T. Baba (Yokohama National University/PECST)

17:25 B-10

Multi-Layer On-Chip Interconnection Using Si Waveguide Devices

N. Nishiyama (Tokyo Institute of Technology/PECST)

Banquet (18:00-20:00): Foyer of Ito International Research Center

November, 19 (Tuesday)

Venue: ENEOS Hall (Oral Sessions & Poster Preview)

Convention Hall (Poster Presentation)

Komaba Research Campus, The University of Tokyo

Session C: Silicon Nanophotonics Devices & Systems II (9:30-11:30)

9:30 **C-1 (Invited)**

Near Infrared Optical Properties of III-V Core-Shell Nanowires on Si

G. Abstreiter (Technical University of Munich)

10:10 C-2 (Invited)

Recent Silicon Photonic Activities in Europe

L. Fulbert (CEA-LETI)

10:50 **C-3 (Invited)**

25Gb/s Silicon-Photonics WDM Platform for Low-Power Optical I/O

J. Van Campenhout (IMEC)

11:30-13:00 Lunch break

Poster Session (13:00-15:45)

13:00 Poster preview

13:55 Poster presentation (core time for the odd-numbered posters)

14:50 Poster presentation (core time for the even-numbered posters)

Session D: Silicon Nanophotonics Devices & Systems III (16:00-17:25)

16:00 **D-1 (Invited)**

MEMS-Based Integration for Optical Systems

K. Hane (Tohoku University)

16:40 **D-2**

Enhancement of Wavelength Characteristic Shift in Si Grating Waveguides

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The 3rd International Symposium on Photonics and Electronics Convergence -Advanced Nanophotonics and Silicon Device Systems-(ISPEC2013)

Tokyo, Japan on 18-20 November, 2013

Notice

November 18, 2013

Venue: Ito International Research Center (IIRC)
Hongo Campus, the University of Tokyo, Tokyo, Japan

November 19-20, 2013

Venue: ENEOS Hall Komaba Research Campus

Komaba Research Campus, the University of Tokyo, Tokyo, Japan

Announcement for overseas students and young researchers

ISPEC will provide some support for travel expenses for selected students and young researchers travelling from overseas.

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Last updated at 2013/08/27